Supplemental Information for

Thermoelectric Enhancement in $BaGa_2Sb_2$ by Zn-Doping

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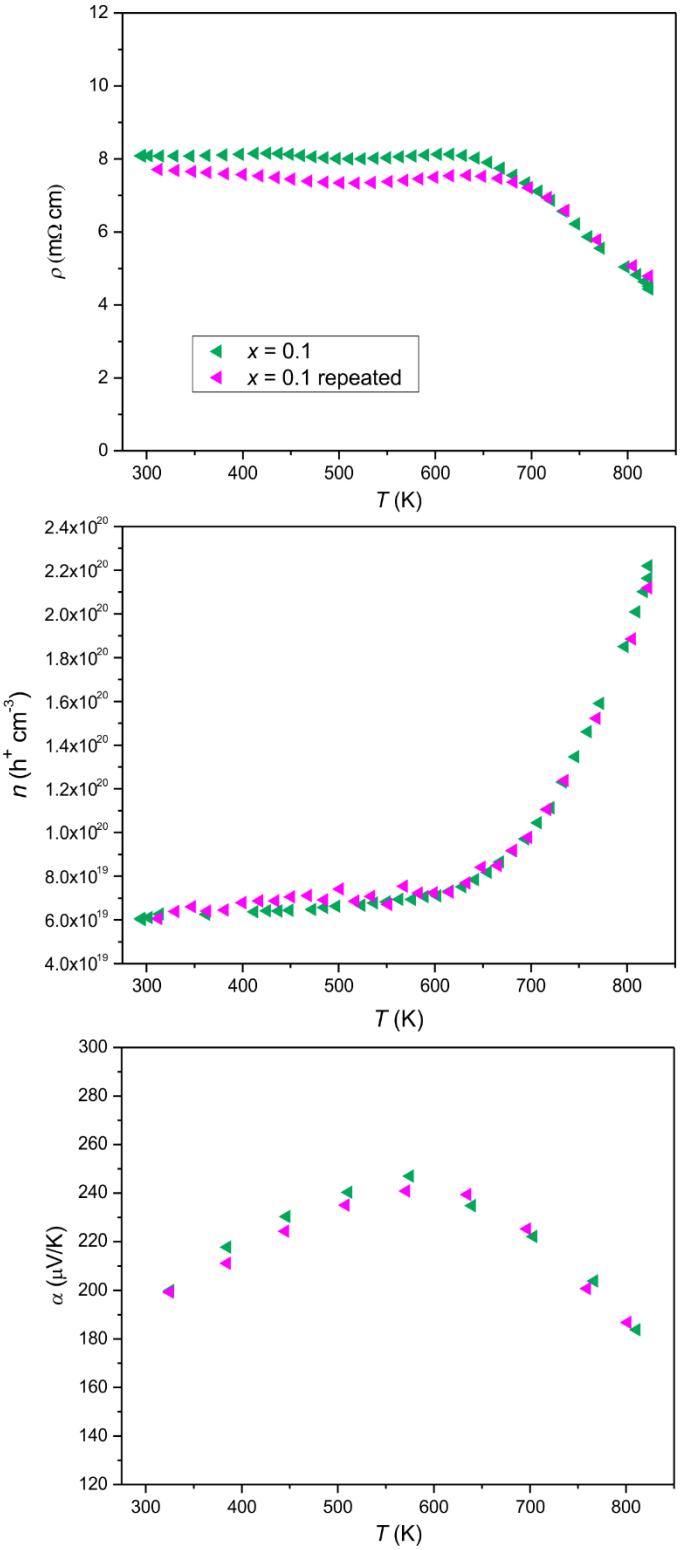

Figure S1: Reproducibility of the transport data was checked for a sample of $BaGa_{2-x}Zn_xSb_2$ with $x = 0.1$. Within experimental accuracy, no difference was observed for the measured properties.

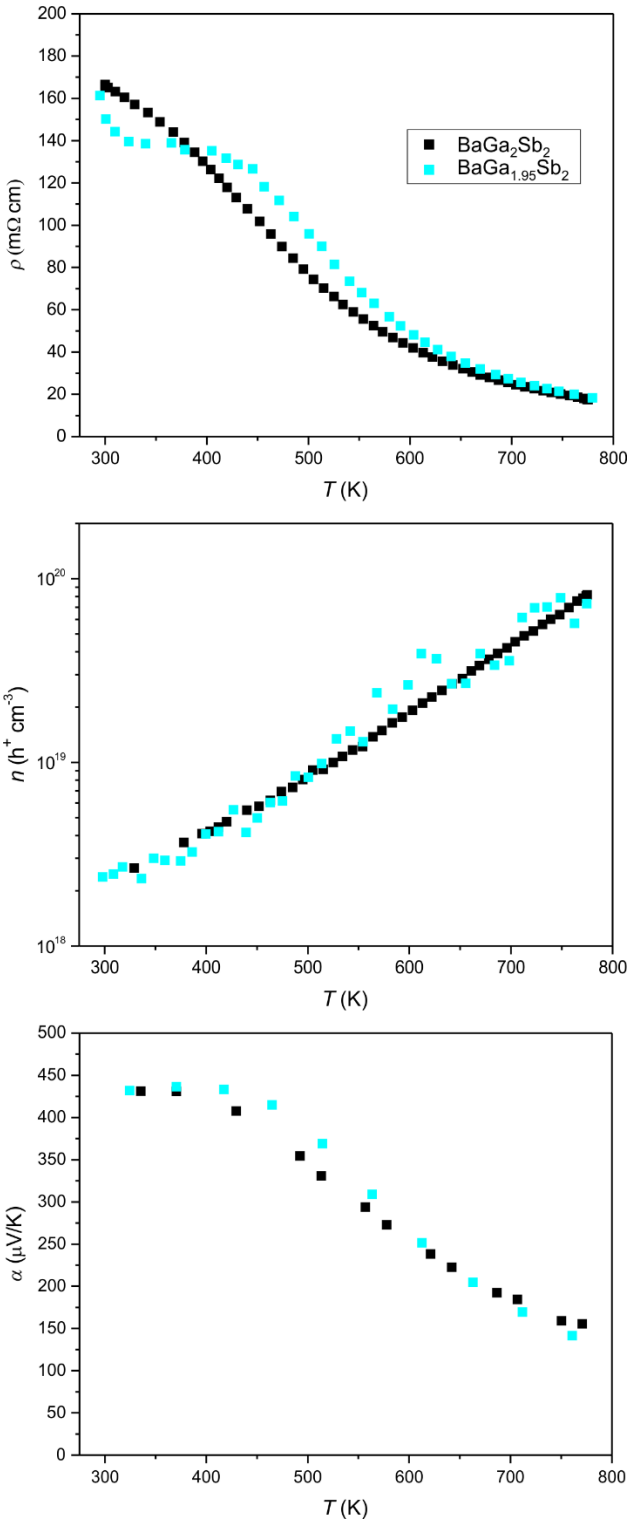

Figure S2. A comparison of the electronic properties of $BaGa_2Sb_2$ and $BaGa_{1.95}Sb_2$ samples. The transport properties of both samples were found to very similar signifying that the increase in carrier concentration is not due to Ga deficiency but Zn doping.